

Title (en)
Semiconductor igniter

Title (de)
Halbleiterzünder

Title (fr)
Allumeur semiconducteur

Publication
EP 0949479 B1 20020918 (DE)

Application
EP 99106969 A 19990409

Priority
DE 19815928 A 19980409

Abstract (en)
[origin: EP0949479A1] The igniter has a thermal insulation layer (104) which is limited to the ignition gap region (108) of a semiconductor layer (106). The semiconductor layer, at its end sections (110,112) held free from the thermal insulating layer, is connected fixed with a carrier (102). The semiconductor layer, is heated, with current passing in the ignition gap region, to trigger the ignition.

IPC 1-7
F42B 3/13

IPC 8 full level
B60R 21/26 (2006.01); **F42B 3/13** (2006.01)

CPC (source: EP US)
F42B 3/13 (2013.01 - EP US)

Cited by
EP1275931A1; US10940341B2; WO02057705A3

Designated contracting state (EPC)
AT ES FR GB IT SE

DOCDB simple family (publication)
EP 0949479 A1 19991013; EP 0949479 B1 20020918; AT E224529 T1 20021015; DE 19815928 A1 19991104; DE 19815928 C2 20000511; ES 2181330 T3 20030216; JP 2000028298 A 20000128; US 6220164 B1 20010424

DOCDB simple family (application)
EP 99106969 A 19990409; AT 99106969 T 19990409; DE 19815928 A 19980409; ES 99106969 T 19990409; JP 10172899 A 19990408; US 28861599 A 19990409